

Homointerface planar Josephson junction based on inverse proximity effect

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Abstract

The quality of a superconductor–normal metal–superconductor (SNS) Josephson junction (JJ) depends crucially on the transparency of the superconductor–normal metal (S/N) interface. We demonstrate a technique for fabricating planar JJs with perfect interfaces. The technique utilizes a strong inverse proximity effect (IPE) discovered in Al/V₅S₈ bilayers, by which Al is driven into the normal state. The highly transparent homointerface enables the flow of Josephson supercurrent across a 2.9 μm long weak link. Moreover, our JJ exhibits a giant critical current and a large product of the critical current and the normal state resistance. The latter exceeds the theoretical bound, which is probably related to the unusual normal metal weak link.

A JJ consists of two superconductors coupled through a weak link and is the fundamental element in a variety of superconducting electronics[1–3]. Depending on the weak link, there are different types of JJs, e.g., superconductor–insulator–superconductor (SIS), SNS and superconductor–narrow constriction–superconductor (ScS) [4]. SNS JJs have a negligible inherent capacitance. Being overdamped, their current–voltage characteristics can be made, in principle, non-hysteretic, which is desired in high frequency applications[5]. Moreover, they have potentially higher $I_c R_N$ value[6], which is the figure of merit in many applications[5, 7]. Here, I_c is the critical current, R_N is the normal state resistance. Recently, the interest in SNS JJs have been intensified, as it has been proposed that such junctions, when N is topologically nontrivial, can be used in topological quantum computing[8]. However, the characteristics of SNS devices are strongly affected by the superconductor–normal metal interface, which poses a challenge in device fabrication. It is also known that disorders in the interface lead to the soft-gap problem[9]. Various techniques have been employed to achieve transparent and consistent interfaces, e.g., shadow deposition[10, 11], *in situ* epitaxial growth[12–14].

Here, we demonstrate a technique for constructing SNS JJs utilizing the IPE. We observed a complete suppression of superconductivity in a 31 nm aluminum film deposited on a 10 nm novel V_5S_8 superlattice film. Using this non-superconducting Al/ V_5S_8 bilayer as the weak link, an aluminum SNS JJ with fully transparent homointerfaces was fabricated. Such junctions exhibit high critical currents and large $I_c R_N$ values.

V_5S_8 superlattice films used in this study were grown by a chemical vapor deposition method on SiO_2 substrates[18]. Devices were patterned using standard e-beam lithography, followed by e-beam deposition of a 2 nm titanium adhesion layer and the aluminum layer of desired thickness. Devices were loaded into an Oxford 3He cryostat with a base temperature of about 250 mK. Low temperature electrical measurements, with multiple-stage low-pass filtering, were carried out using a lock-in amplifier.

The compound of V_5S_8 known in the literature is VS_2 layers self-intercalated with vanadium[19]. It becomes an antiferromagnet below 32 K[20]. In stark contrast, V_5S_8 used in this study has a unique superlattice structure consisting of VS_2 layers intercalated with V_2S_2 atomic chains[18], seen in the Supplementary Material. It shows no indication of either ferromagnetism or antiferromagnetism. More interestingly, the new V_5S_8 displays an exotic in-plane Hall effect that has not been reported before. This effect results from an

out-of-plane Berry curvature induced by the in-plane magnetic field, enabled by a peculiar anisotropic spin-orbit coupling. For simplicity, we still use the chemical formula of V_5S_8 in this letter to refer to the new material.

A bilayer device S1, Al(31)/ V_5S_8 (10), is illustrated in the inset of Fig. 1a. The number in the parenthesis denotes the thickness in nanometer. The superconducting transition temperature T_{cs} of a 31 nm Al film on the SiO_2 substrate, defined by the midpoint of the resistance transition, is 0.72 K. Surprisingly, S1 remains in the normal state down to 0.28 K. Not even a slight depression of the resistance was observed, indicating that the superconductivity of 31 nm Al was completely destroyed by 10 nm V_5S_8 . To get an idea of the strength of the IPE, we fabricated more bilayer devices, in which the thickness of the Al film is varied, while maintaining the same V_5S_8 thickness as in S1. As shown in Fig. 1b, superconductivity gradually recovers with increasing Al thickness. When the Al film is 96 nm, superconductivity is fully restored. We compare our experimental data with the classical theory describing the proximity effect in the S/N bilayer[21–23]. The detailed calculation can be found in the Supplementary Material. As shown in Fig. 1c, the experimental data are well below the theoretical calculation, suggesting the IPE induced by V_5S_8 on the Al film is too strong to be explained by the classical theory of the S/N proximity system.

When the superconductor layer in an S/N bilayer is thin, the system is non-superconducting due to the IPE. As the thickness of the superconductor layer increases to a critical value $d_{cr,s}$, superconductivity will appear. Therefore, $d_{cr,s}/\xi_s$ may be used to estimate the strength of IPE. In Fig. 1f, we compare $d_{cr,s}/\xi_s$ of our Al/ V_5S_8 bilayer with some S/N and superconductor/ferromagnet systems. In a Pb/Cu bilayer $d_{cr,s}/\xi_s = 0.025$ [15], consistent with a weak IPE described by classical theories. For ferromagnetic films, Ni and Co, $d_{cr,s}/\xi_s$ can reach 1.14 and 1.42, respectively[17]. For our Al/ V_5S_8 bilayer, $0.35 < d_{cr,s}/\xi_s < 0.73$ (calculated from Fig. 1c). It is remarkable that the IPE of Al/ V_5S_8 bilayer is even stronger than the (Co/Pd)₁₀ film[16].

The IPE is intriguing and deserves further investigation. In this work, we focus on an application of the effect in JJs. Utilizing the observed strong IPE, an Al–(Al/ V_5S_8)–Al planar JJ can be fabricated using a simple one-step metal deposition process. Shown in Fig. 2a, a narrow V_5S_8 flake and an Al strip form a cross. Non-superconducting Al on V_5S_8 plays the role of a weak link between superconducting Al electrodes on the SiO_2 substrate, which creates an SNS junction. Since the junction is built with a single piece of

continuous Al film, the homointerface is supposedly fully transparent. As Al(31)/V₅S₈(10) is non-superconducting at the lowest temperature of this experiment, the JJs studied below are all based on Al(31)/V₅S₈(10) bilayers. The temperature dependence of the resistance for JJ S4 shows that the Josephson supercurrent is established below 0.7 K. The differential resistance dV/dI of the device displays clear diffraction patterns in the magnetic field versus bias current mapping (Fig. 2c). In this Fraunhofer pattern, the characteristic of a JJ, at least eight side lobes can be identified, suggesting a homogeneous junction with highly transparent interfaces. Note that similar JJs based on a cross structure have been demonstrated, using the IPE of ferromagnetic metals [25, 26]. However, the Fraunhofer pattern displays irregularities in amplitude and frequency. These features imply substantial inhomogeneities, probably stemming from grain or domain structures in the ferromagnetic layer. Our V₅S₈ samples are single crystals and non-magnetic, enabling the formation of a uniform weak link.

The oscillating critical current $I_c(B)$ can be described by $I_c(B) = I_c(0) \left| \frac{\sin(\pi BS/\Phi_0)}{\pi BS/\Phi_0} \right|$, where B is the perpendicular magnetic field, S is the effective area of junction, $\Phi_0 = h/2e$ is the flux quantum. Let $B^{(n)}$ denote the magnetic field when I_c lies at the local minimum of the Fraunhofer pattern. The node index n is equal to the number of flux quantum penetrating the junction. We define $n < 0$ if $B < 0$. The linear relationship between $B^{(n)}$ and n reflects equally spaced nodes in the pattern (Fig. 2d). The slope ΔB is 0.55 mT. $\Phi_0/\Delta B = 3.8 \mu\text{m}^2$ yields the effective area of the junction. In comparison, the nominal area of Al(31)/V₅S₈(10) is $3.0 \mu\text{m}^2$. The discrepancy can be ascribed to the London penetration depth and flux-focusing [27].

The good quality of the junction S/N interface enables the establishment of a Josephson supercurrent across large gaps of the weak link. Fig. 3b shows a zero resistance state and a finite supercurrent in a junction with a $2.9 \mu\text{m}$ gap. Likely for the same reason, our junction can support a giant supercurrent even when the gap is relatively large. Fig. 3d shows the Fraunhofer pattern of a device with a $0.9 \mu\text{m}$ gap. The supercurrent reaches $255 \mu\text{A}$ in zero magnetic field at 0.26 K ($\sim 0.32T_c$), yielding a large supercurrent density of $2.1 \times 10^5 \text{ A/cm}^2$ among SNS junctions [28–30]. The critical current of the junction is so large that the superconductivity of Al electrodes is quenched by the Joule heating as soon as the junction goes into the normal state, which will be explained shortly.

Because of the device structure, the measured junction resistance is a sum of the actual junctions resistance and the resistances of Al segments between two voltage probes, as seen

in the inset of Fig. 2b. Consequently, as the bias current increases, two sequential resistance transitions are expected. The first one indicates the critical current of the junction, while the second one is the critical current of Al electrodes, I_c^{Al} . This is what is observed above 1.5 mT, seen in Fig. 3d. The critical current line of Al encloses the Fraunhofer pattern. There are 0.4Ω for the normal state resistance of junction and 4.3Ω for the electrode resistance. However, below 1.5 mT, the zeroth and first diffraction peaks protrude over the Al critical current. In particular, the maximum of the zeroth peak exceeds the Al critical current by 4.8 times. This bizarre result seems to indicate that the Al electrode can sustain a much higher supercurrent when the junction is also in the superconducting state than that when the junction is non-superconducting. We believe that, rather than I_c^{Al} being enhanced in the protruding regions, I_c^{Al} is strongly suppressed in other regions because of the Joule heating occurring at the junction when it goes into the normal state. When the critical current of junction is higher than the suppressed I_c^{Al} , two transitions take place simultaneously, leading to only one resistive transition in the protrusion regions. At a higher temperature, $T = 0.67$ K, the critical current of junction is reduced more strongly than I_c^{Al} . The whole Fraunhofer pattern submerges below I_c^{Al} and a common two-transition pattern appears, shown in Fig. 3e.

Transparent interfaces in SNS JJs are critical for obtaining a large $I_c R_N$, which is an important parameter of JJs. Shabani et al. improved the interface by employing epitaxial growth of aluminum on a semiconductor and achieved $I_c R_N \sim 0.68\Delta/e$ at very low temperature, $T/T_c = 0.02$ [13]. Here Δ is the superconducting gap of the superconductor. We plot $I_c R_N$ of JJ S6 as a function of temperature in Fig. 4. At 0.26 K ($T/T_c = 0.32$), $I_c R_N \approx 0.81\Delta/e$ is obtained. This value is anticipated to be substantially enhanced with decreasing temperature[31]. Generally speaking, $I_c R_N$ is bounded by the minimum of Δ and the Thouless energy E_{Th} , where $E_{\text{Th}} = \hbar D/L^2$ [31]. Here L is the junction length, D is the diffusion constant and can be calculated by $D = \frac{1}{3}(\frac{\pi k_B}{e})^2 \frac{\sigma}{\gamma}$ [32]. With the electronic specific heat coefficient $\gamma = 140 \text{ J}\cdot\text{m}^{-3}\cdot\text{K}^{-2}$ and the electrical conductivity $\sigma = 4.5 \times 10^7 \text{ S}\cdot\text{m}^{-1}$ in the normal state, E_{Th} of JJ S6 turns out to be $6.5 \mu\text{eV}$, much less than Δ . In this long-junction limit, detailed theoretical calculations showed that the upper bound of $I_c R_N$ at zero temperature is $10.82E_{\text{Th}}/e$ [31]. Surprisingly, our $I_c R_N \sim 15.3E_{\text{Th}}/e$ at an intermediate temperature of 0.26 K, already exceeding the theoretical bound. Taken into account the approximate linear temperature dependence of $I_c R_N$ [31], it may even become substantially higher at low temperatures. The weak link of our JJs is made of a superconductor, of which

the superconductivity is killed by the IPE. The giant $I_c R_N$ is most likely related to the unusual nature of the weak link.

The high transparency of the interface of our JJs is also reflected in the excess current, defined by $I_{\text{ex}} = I - V/R_N$. I_{ex} can be obtained by extrapolating the linear dependence of the I - V characteristic in the normal state to the I axis. The higher the interface transparency, the higher probability the Andreev reflection occurs at, hence the larger I_{ex} [33]. The inset of Fig. 3f shows $I_{\text{ex}} \approx I_c$, implying highly transparent interfaces.

In conclusion, we observed a strong IPE in a bilayer of Al/ V_5S_8 . Based on the effect, a Josephson junction with superconductor-normal metal homointerface can be readily fabricated. Owing to the highly transparent interface, the junction displays a large critical current and $I_c R_N$ product, showing potentials in superconducting electronic applications.

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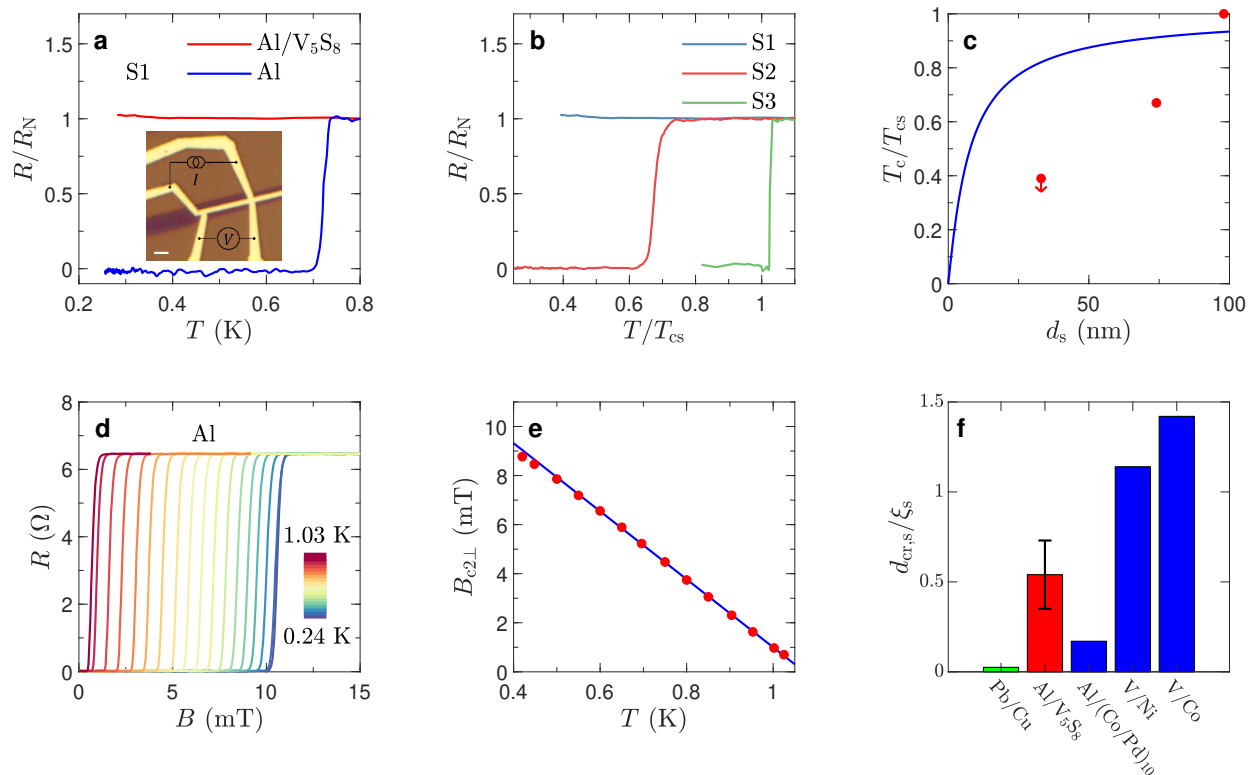


FIG. 1. IPE in bilayer of Al/ V_5S_8 . (a) Temperature dependence of the resistance for a 31-nm-thick Al film on V_5S_8 (device S1) and SiO_2 . The resistance R is normalized by R_N . The inset is an illustration of the four-probe measurement of device S1. The scale bar represents $2\ \mu m$. (b) Normalized R versus T for device S1, S2 and S3. The Al thicknesses in these devices are 31, 72 and 96 nm, respectively. T is normalized by T_{cs} , the transition temperature of the corresponding Al film on the SiO_2 substrate. (c) Normalized transition temperature T_c/T_{cs} versus thickness d_s of Al in Al/ V_5S_8 bilayer system. Dots with arrow denote the upper limit of the critical temperature as the device is not superconducting down to the lowest temperature of this study. The solid line represents the result of the Werthamer theory on the proximity effect in the S/N bilayer. (d) R - B curves of 72-nm-thick Al film on the SiO_2 substrate at different temperatures. (e) The linear- T dependence of $B_{c2\perp}$. (f) Comparison of $d_{cr,s}/\xi_s$ in Al on V_5S_8 with those in Pb/Cu [15], $Al/(Co/Pd)_{10}$ [16], V/Ni and V/Co [17].

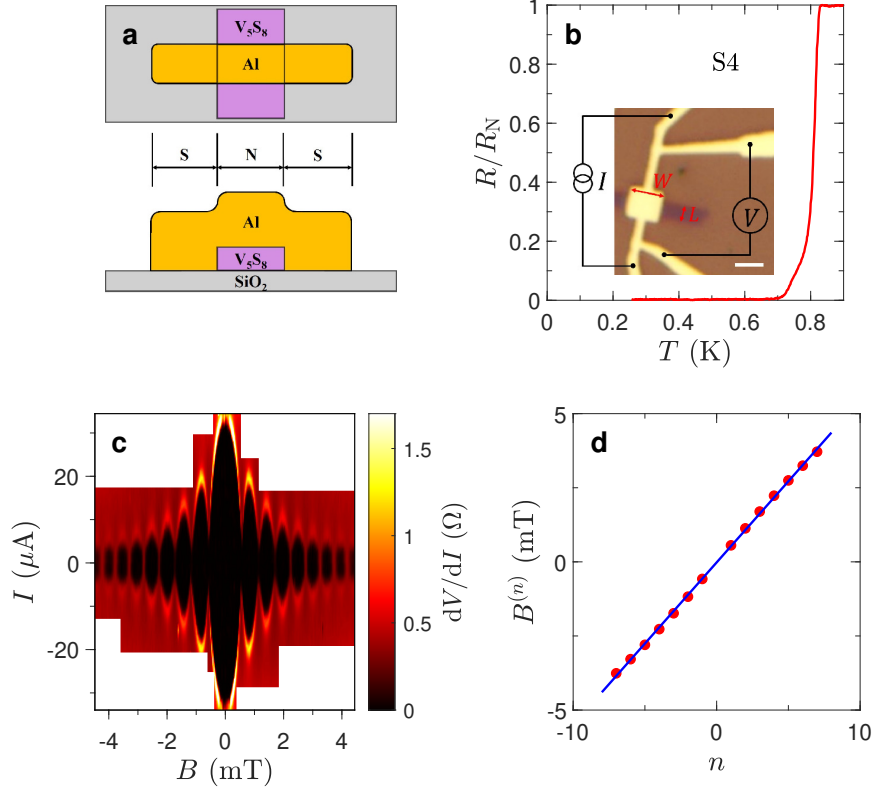


FIG. 2. Homointerface planar JJ based on IPE. (a) The top view and the side view of the schematic of an Al–(Al/V₅S₈)–Al JJ. (b) Normalized resistance R as a function of T for device S4. The inset is an optical micrograph of S4 with an illustration of the measurement configuration. The junction length L is $1.1 \mu\text{m}$, the junction width W is $2.7 \mu\text{m}$. The scale bar is $2 \mu\text{m}$. $0.6 \mu\text{m}$ away from the junction, the width of the Al superconductor is reduced to $0.8 \mu\text{m}$ so that no vortices can enter[24]. Otherwise, flux jumping will appear in the Fraunhofer pattern. (c) Fraunhofer diffraction pattern at 0.25 K . (d) The magnetic field of the nodal point extracted from (c). The solid blue line is a linear fit.

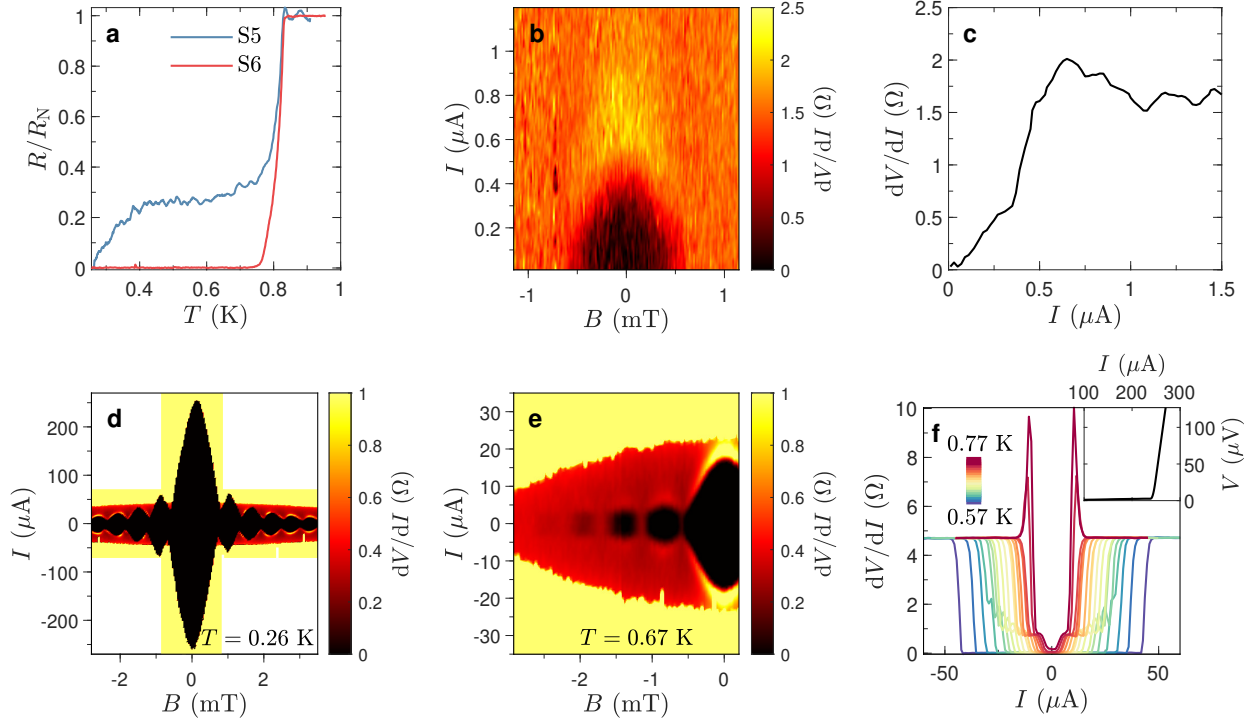


FIG. 3. Properties of JJ S5 and S6. $L = 2.9 \mu\text{m}$ and $W = 1.6 \mu\text{m}$ for S5. $L = 0.9 \mu\text{m}$ and $W = 2.8 \mu\text{m}$ for S6. (a) Normalized R versus T . (b) Two dimensional mapping of the differential resistance dV/dI in the I - B plane for S5 at 0.26 K. (c) dV/dI versus I at $B = 0$ extracted from (b). (d) and (e) Fraunhofer diffraction pattern of S6 at 0.26 K and 0.67 K, respectively. (f) dV/dI versus I for S6 at different temperatures ranging from 0.57 to 0.77 K. The inset is the I - V characteristic at 0.26 K.

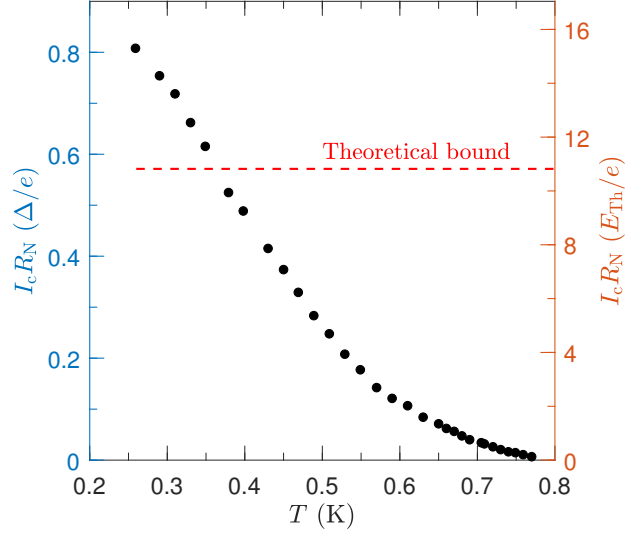


FIG. 4. $I_c R_N$ of JJ S6 scaled by Δ and E_{Th} as a function of temperature. The red dashed line indicates the theoretical bound of $10.82E_{Th}/e$ [31].

Supplemental Materials: Homointerface planar Josephson junction based on inverse proximity effect

This Supplemental Material Section contains the crystal structure of V_5S_8 and detailed calculation of the proximity effect in the Al/ V_5S_8 bilayer.

Crystal structure of superlattice V_5S_8

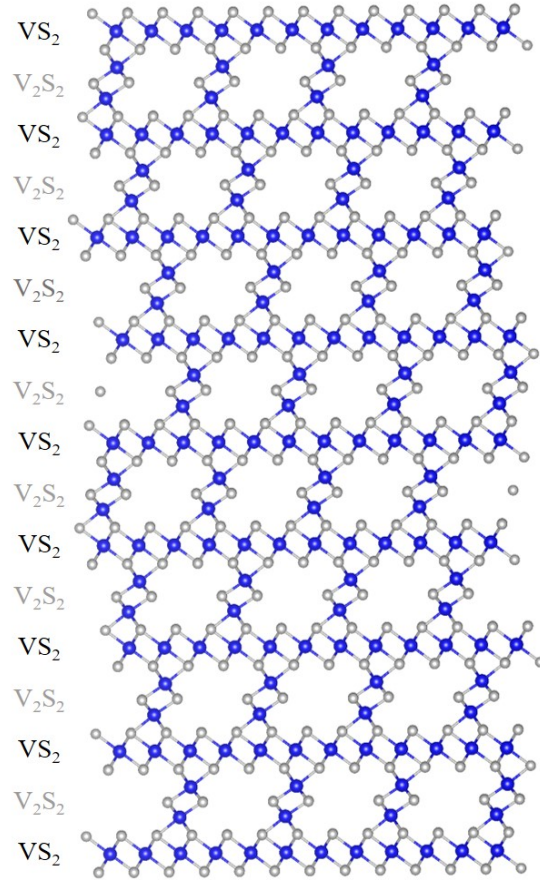


FIG. S1. Atomic structure of the V_5S_8 superlattice in side view.

The crystal structure of the superlattice V_5S_8 has a triclinic symmetry and belongs to the space group of P1, with lattice constants of $a = 9.69 \text{ \AA}$, $b = 3.23 \text{ \AA}$, $c = 75.53 \text{ \AA}$, $\alpha = \beta = 90^\circ$ and $\gamma = 120^\circ$. Fig. S1 depicts the atomic structure of the V_5S_8 superlattice in side view. One can see that VS_2 layers are intercalated with V_2S_2 atomic chains, which are oriented perpendicular to the plane of paper.

Calculation of the proximity effect based on the Werthamer theory

According to the theory by Werthamer, the proximity effect in the one-dimension S/N bilayer can be described by a set of three equations[S21–S23]:

$$-\chi(-\xi_n^2 k_n^2) = \ln(T_c/T_{cn}) \quad (\text{S1})$$

$$\chi(\xi_s^2 k_s^2) = \ln(T_{cs}/T_c) \quad (\text{S2})$$

$$[N\xi^2 k \tan(kd)]_s = [N\xi^2 k \tanh(kd)]_n \quad (\text{S3})$$

. Here T_c is the transition temperature of the S/N bilayer, T_{cs} and T_{cn} are the transition temperatures of the superconductor and the normal metal, respectively. ξ_s is the superconducting coherence length of the superconductor and ξ_n is the depth by which Cooper pairs penetrate into the normal metal. $\chi(Z) = \psi(\frac{1}{2} + \frac{1}{2}Z) - \psi(\frac{1}{2})$, where ψ is the digamma function. $k_{s,n}$ are free parameters, N is the density of state, d is the thickness. Eqs. (S1) and (S2) describe the properties of normal metal and superconductor, respectively. Eq. (S3) is the boundary condition at the S/N interface.

Since V_5S_8 is a normal metal, $T_{cn} = 0$. Plugging it into Eq. (S1), we get $-\chi(-\xi_n^2 k_n^2) = +\infty$, so $k_n = 1/\xi_n$. Using this relation, Eq. (S3) becomes

$$[N\xi^2 k \tan(kd)]_s = [N\xi \tanh(d/\xi)]_n \quad (\text{S4})$$

. For a nonmagnetic diffusive system, $\xi_n = (\hbar D_n/2\pi k_B T)^{1/2}$, where D_n is the diffusion coefficient[S34]. Generally, ξ_n is much larger than $d_n = 10$ nm[S35], so Eq. (S4) can be approximated to

$$[N\xi^2 k \tan(kd)]_s = [Nd]_n \quad (\text{S5})$$

. Assuming V_5S_8 and Al as free electron systems, we have $N_n/N_s = (n_n/n_s)^{1/3}$, where n is the carrier density. For Al, $n_s = 1.806 \times 10^{29} \text{ m}^{-3}$, while for V_5S_8 , $n_n = 4.161 \times 10^{27} \text{ m}^{-3}$, determined from the Hall resistivity[S18]. Then, N_n/N_s is equal to 0.2846. According to the Ginzburg-Landau theory, the perpendicular upper critical field $B_{c2\perp}$ of the superconducting film is linear with the temperature T as $B_{c2\perp}(T) = B_{c2\perp}(0)(1 - T/T_c)$ near T_c . ξ_s is related to $B_{c2\perp}(0)$ via $\xi_s = \frac{1}{\pi}(\frac{2\Phi_0}{\pi B_{c2\perp}(0)})^{1/2}$, where $\Phi_0 = h/2e$ is the flux quantum[S36]. Therefore, we find that ξ_s is about 102 nm. Finally, Eq. (S5) is reduced to

$$[k \tan(kd)]_s = 2.846 \times 10^{-4} \text{ nm}^{-1}. \quad (\text{S6})$$